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Original article

Detection of magnetic nanoparticles using simple AMR sensors in Wheatstone bridge

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Wheatstone bridges incorporating a serially connected ensemble of simple AMR elements of $Ni_{80}Fe_{20}$ film were produced, targeting an application of a pinned magnetic field along the sensing magnetoresistor length. For the optimal dimension, the magnetoresistive element with length $l = 4$ mm, width $w = 150$ μm and thickness $t = 5$ nm still shows a rather modest AMR ratio (of about 0.85% only). However, the resulting bridge exhibits a sensitivity as large as 2.15 mV/Oe. This is according to a standard sensitivity of 1.80 mV/V/Oe and a detection limit better than 10^{-6} emu, which is almost doubled with respect to that in the typical commercial AMR devices and is comparable with Permalloy based PHE sensor. This is suitable to detect the superparamagnetic fluid of 50 nm-Fe_3O_4-chitosan.

1. Introduction

Spintronic sensors have been becoming increasingly important not only in industrial domains, but also in biomedical applications. For latter interests, the magnetic microbeads or nanoparticles are labeled with biomolecules and are employed in detecting target by binding the probe biomolecules immobilized on the magnetic sensing surface. Accordingly, magnetic sensing micro-bioassays have been developed on the basis of anisotropic magnetoresistive (AMR), giant magnetoresistive (GMR), magnetic tunnel junction (MTJ) and/or planar Hall effect (PHE) sensors [1,2]. In such applications, the magnetic field sensitivity of about 10 μV/Oe and the detection limit of 2×10^{-10} emu is required [2,3]. In addition, the stability of the sensor output must be ensured over a large range of temperatures and, in general, the signal to noise (*S/N*) ratio must be suppressed. These demands are usually improved thanks to integrating the sensors in Wheatstone bridge configuration, which can provide a null-voltage output in the absence of an external stimulation field, while ensuring the same full output voltage of a single device [4–6]. Practically, a classic Wheatstone bridge was designed based on typical 0°–90° AMR magnetoresistors [4]. The replacement of AMR by MTJ sensors resulted in devices with enhanced magnetic field sensitivity of 32 mV/V/Oe [5], which strongly overcomes the sensitivity of 1 mV/V/Oe in the typical commercial products integrating AMR devices in bridge configuration. Recently, the possibility to use the Wheatstone bridge of exchange-biased GMR spin valve sensors for the detection of 10-nm iron oxide nanoparticles with the concentration of 10 ng/ml was reported [6]. This makes the spintronic sensors rather suitable for use as a biomedical detector.

In this paper, we investigated the possibility of detecting superparamagnetic 50-nm iron oxide nanoparticle utilizing simple AMR sensors in Wheatstone bridge. Here, the low field magnetic sensitivity of AMR bridge device is enhanced by optimizing the dimension of single magnetoresitors correspondingly to their shape magnetic anisotropy.

2. Experimental

The 4 mm-length AMR elements of $Fe_{80}Ni_{20}$ Permalloy with different wide ($w = 150$, 300 and 450 μm) and thickness ($t = 5$, 10 and 15 nm) and respective AMR Wheatstone bridges (see *e.g.* in Fig. 1) were fabricated by using magnetron sputtering technology (*Model ATC* 2000) and the UV Lithography technology (*Model MJB*4). The top Ta layer thickness is of 5 nm. During sputtering process, the magnetic uniaxial anisotropy of single AMR elements was established thanks to a permanent magnet which generated a pined magnetic field of $H_{pin} = 900$ Oe along the sensing R_1 and R_3 magnetoresistor length (Fig. 1c). The pinning degree on this resistor

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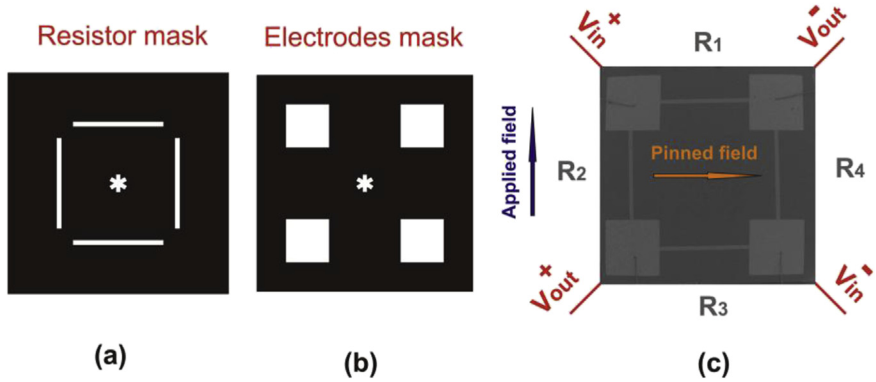

Fig. 1. Fabrication process of AMR elements and complete AMR Wheatstone bridges: (a) resistor mask, (b) electrodes mask, (c) image of fabricated sensor and respective Wheatstone bridge.

pair is different with respect to that on (R_2, R_4) ones due to the shape magnetic anisotropy. Thus, in applied fields, the resistance in (R_1, R_3) and (R_2, R_4) pairs is varied in different ways.

For magnetoresistance measurement, the *dc* precision current source was supplied by using *Keithley* 6220 and the output voltage (V_{out}) was recorded by *Keithley* 2000 multimeter. The V_{out} voltage of the Wheatstone bridge was detected by DSP lock-in amplifier (*Model 7265 of Signal Recovery*) combining with an oscilloscope (*Tektronic DP* 4032).

The output voltage is created due to the different resistance changes. In this case, the change in output voltage (ΔV_{out}) of the Wheatstone bridge is given as

$$\Delta V_{out} = V_{\rm in}(R_1 - R_2)/(R_1 + R_2)$$

where $V_{\rm in}$ is the input voltage and $R_1 = R_3$, $R_2 = R_4$.

In the measuring setup, a *dc* current was applied to the Wheatstone bridge for output voltage measurements. For small resistance change, this constant-current mode is preferred to have more linear response and higher sensitivity (than using constant-voltage mode) [7].

3. Results and discussions

3.1. AMR of magnetoresistive elements

The field dependence of AMR ratio was investigated for a single 4 mm-length AMR element of FeNi with different width ($w = 150$, 300 and 450 μm) and thickness ($t = 15$ nm). The data were recorded with the supplied current of 1 mA and in external magnetic fields applied perpendicular to the pinned magnetic field direction. Here, the ARM ratio is given as

$$AMR(\%) = \frac{\Delta R}{R_{\rm min}} = \frac{R(H) - R_{\rm min}}{R_{\rm min}} = \frac{V(H) - V_{\rm min}}{V_{\rm min}}$$

Presented in Fig. 2 is AMR data measured for the sensing magnetoresistor, which is pinned along the sensor length (i.e. R_1 and/or R_3). It can be seen from this figure that for samples of the same length and thickness, the wider resistor bar, the lower AMR effect is obtained. Indeed, only the highest AMR of 0.34% was found in the sample with $w = 150$ μm. The AMR decreases down to 0.15% for $w = 450$ μm. Similarly, the slope of AMR curves also decreases with increasing *w*. This finding may reflect a well established uniaxial magnetic anisotropy (along the length and/or pinned direction) in resistor elements having a small demagnetizing factor, *i.e.* small *w* demension. A much worse AMR is found for the magnetoresitors,

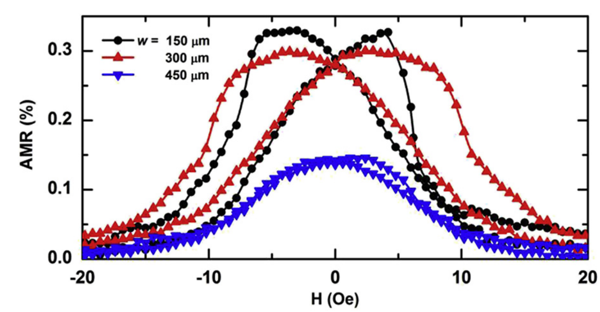

Fig. 2. Magnetic field dependence of AMR ratio measured in external fields applied along the pinned direction for single 4 mm-length AMR elements of FeNi with different width ($w = 150$, 300 and 450 μm) and thickness ($t = 15$ nm).

where the pinned field is perpendicular to the sensor length (*i.e.* R_2 and/or R_4).

The AMR is enhanced in thinner films. For the optimal dimension, the magnetoresistive element with length $l = 4$ mm, width $w = 150$ μm and thickness $t = 5$ nm exhibits a modest AMR ratio of about 0.85%.

3.2. Wheatstone bridge output voltage

As already reported above, in all single magnetoresistive elements under investigation, the AMR signal is not so stable (see *e.g.* Fig. 1). Principally, this is considered as a partial contribution from the thermal noise. It can usually be solved by integrating magnetoresistors in Wheatstone bridge configuration as designed and fabricated in Fig. 1. In this case, the output signals recorded at a supplied current of 1 mA are illustrated in Fig. 3a for AMR Wheatstone bridge integrating single 4 mm-length AMR elements of FeNi with different width ($w = 150$, 300 and 450 μm) and thickness ($t = 15$ nm). Their respective magnetic field derivative dV/dH is presented in Fig. 3b. Clearly, higher stable data are observed. The output voltage of 1.63 mV and maximal sensitivity of 0.24 mV/Oe are found for the Wheatstone bridge with 450 μm width AMR sensors. They strongly increase up to 3.28 mV and 1.05 mV/Oe, respectively, in the 150 μm width sensors.

The NiFe-layer thickness dependence of the output voltage was investigated in three of constant 4 × 0.45 mm area sensors with $t = 5$, 10 and 15 nm. The results are shown in Fig. 4. It can be seen that the thinner NiFe layer, the higher output signal and sensitivity are obtained. Indeed, for the device with $t = 5$ nm, the highest output voltage change $\Delta V = 3.98$ mV and sensitivity $S_{\rm H} =$ (dV/